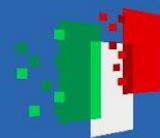




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Italiadomani
PIANO NAZIONALE
DI RIPRESA E RESILIENZA



NQSTI
National Quantum Science
and Technology Institute

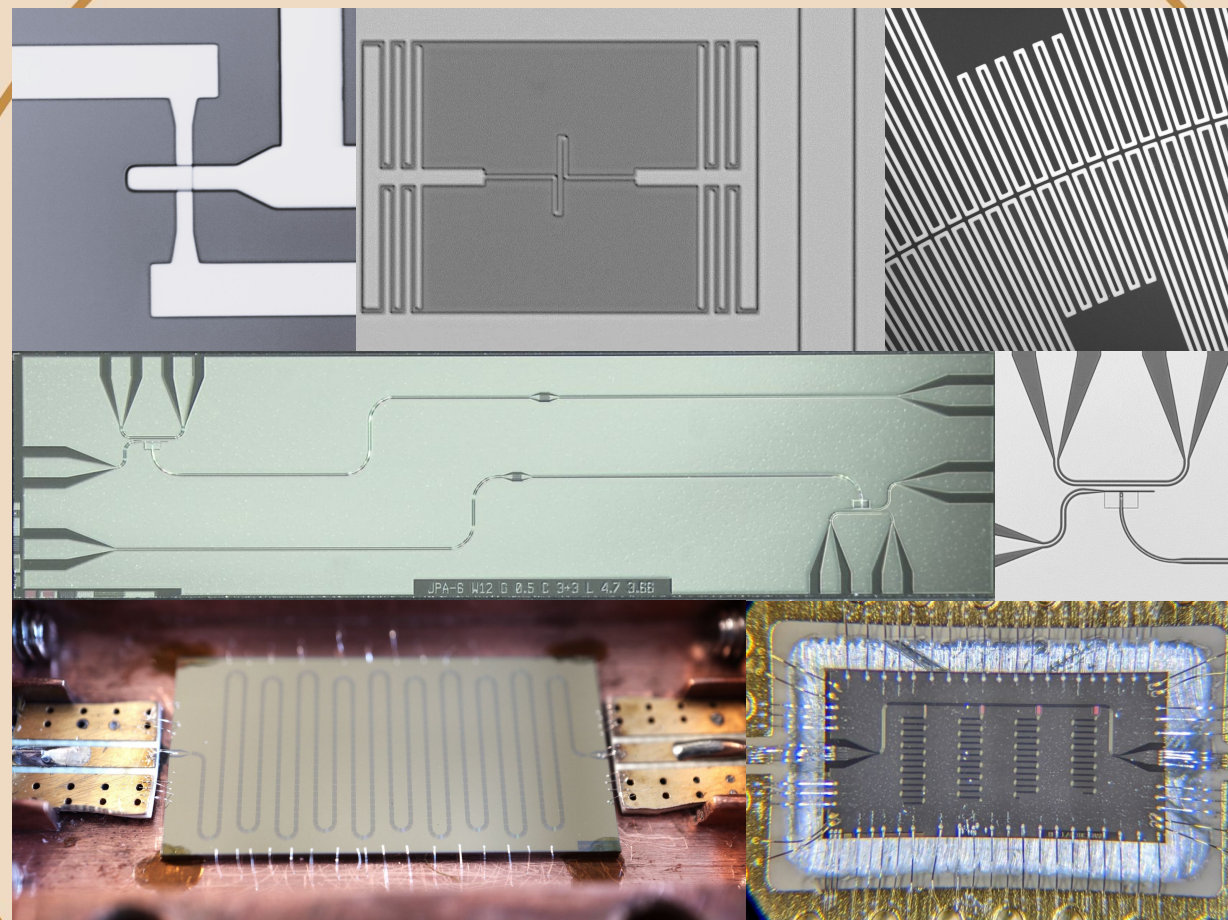
From **single
superconducting components**
to **integrated
qubit circuits**:

Vertical Josephson junctions,
low-loss superconducting resonators
and high-kinetic inductance films

Felix Klaus Ahrens

Fondazione Bruno Kessler (Trento)
Centre for Sensors and Devices

fahrens@fbk.eu
www.fbk.eu

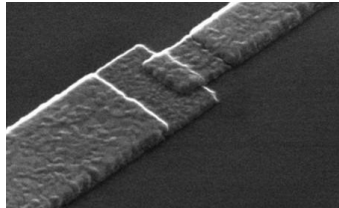


First NQSTI Congress, 15-16 January 2024, Rome

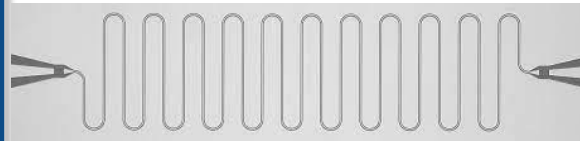


Superconducting electronics - from building blocks to integrated circuits

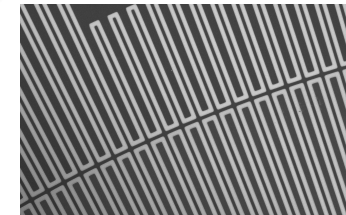
Josephson junctions



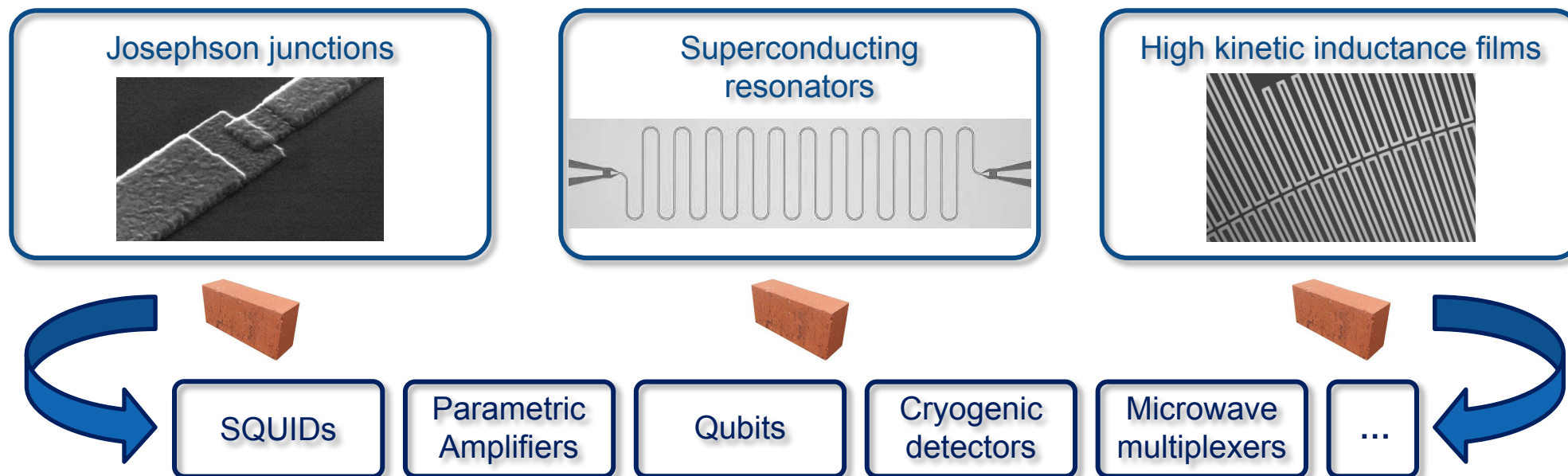
Superconducting
resonators



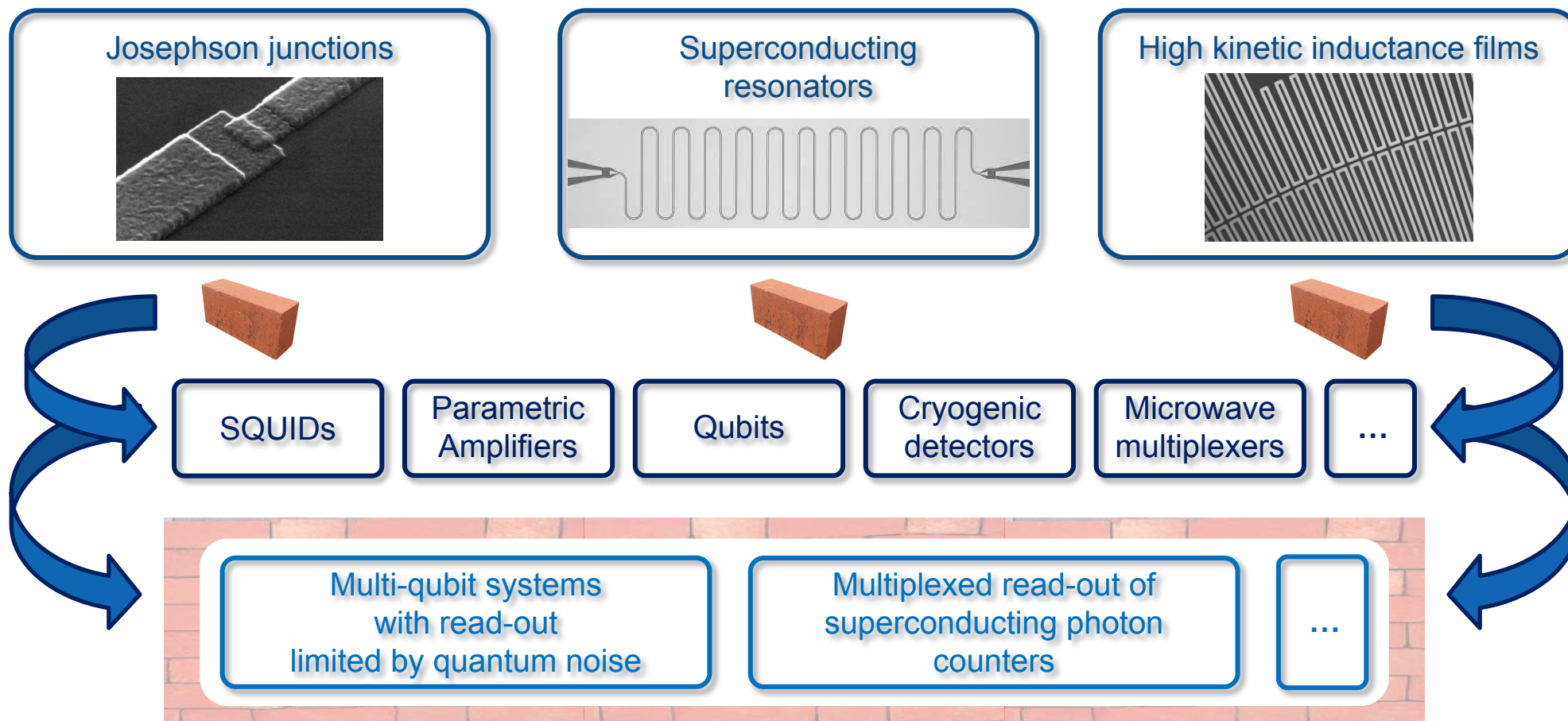
High kinetic inductance films



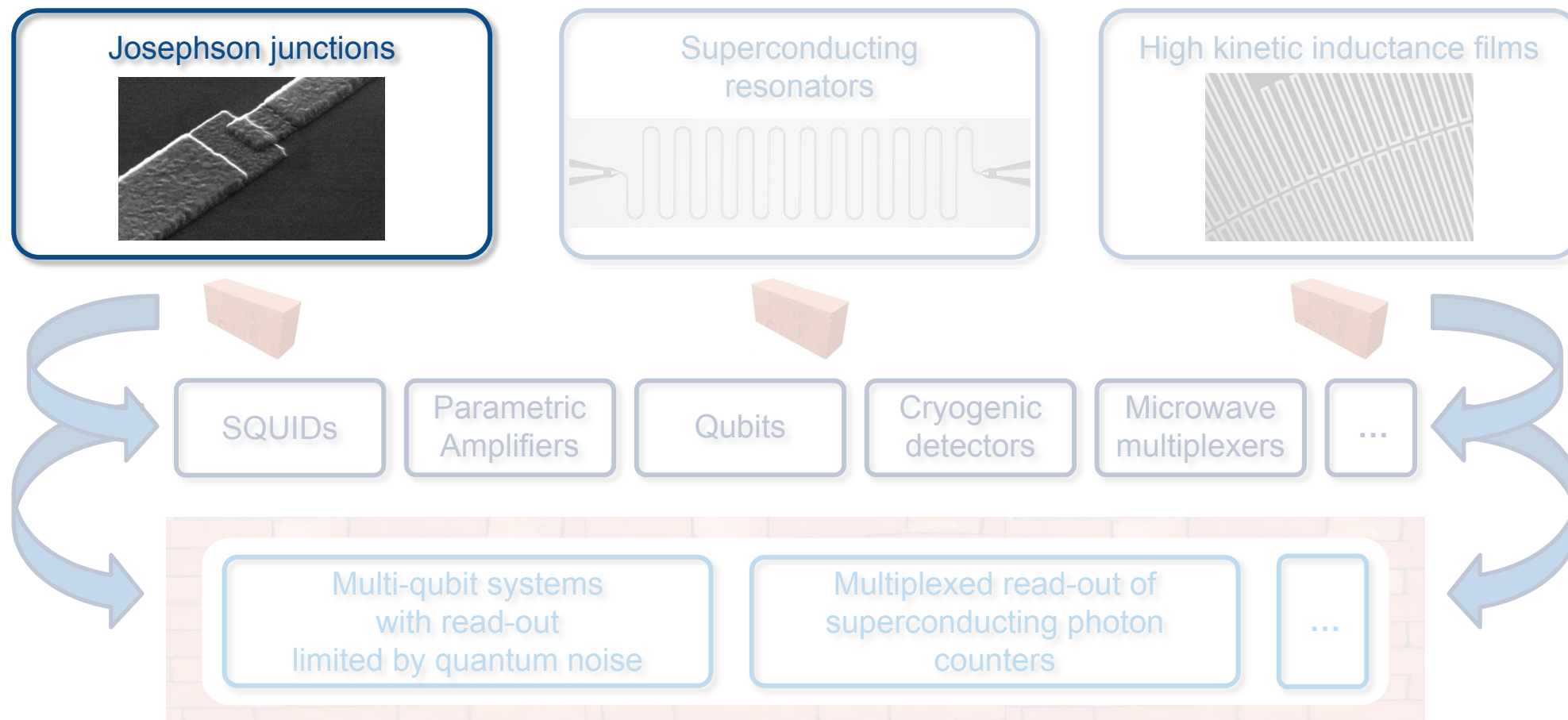
Superconducting electronics - from building blocks to integrated circuits



Superconducting electronics - from building blocks to integrated circuits

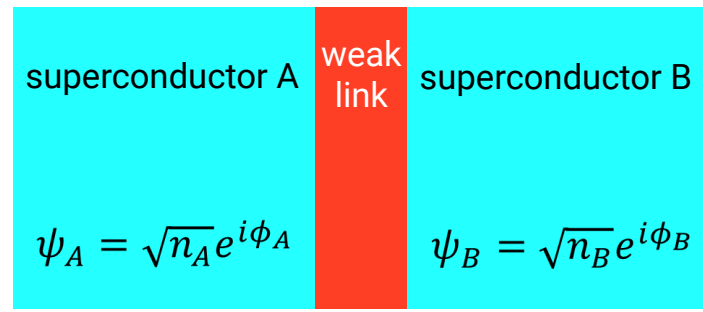


Superconducting electronics - from building blocks to integrated circuits

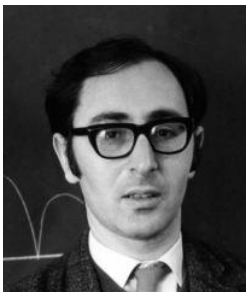




Josephson junctions



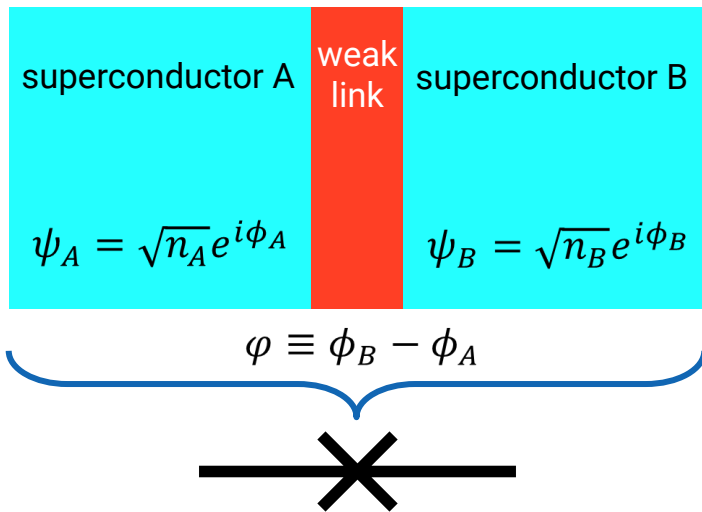
$$\varphi \equiv \phi_B - \phi_A$$



Brian Josephson



Josephson junctions

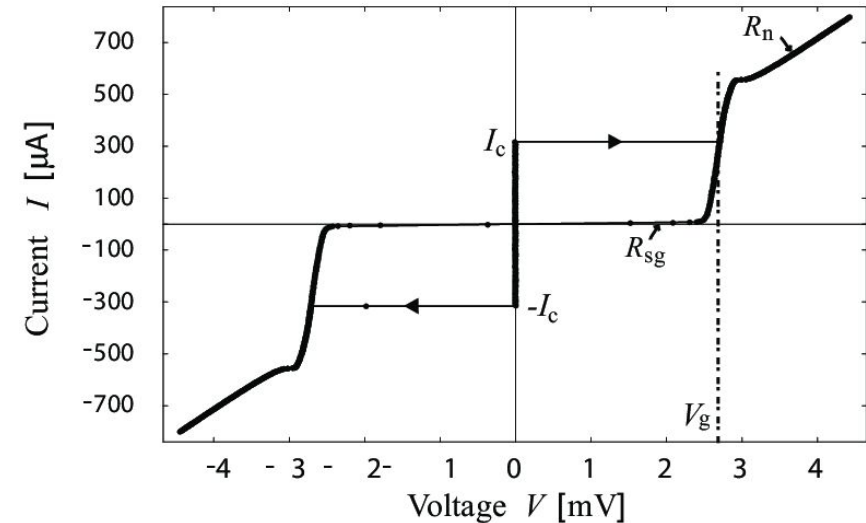


Brian Josephson

Josephson equations

$$I(t) = I_c \sin(\varphi(t))$$

$$\frac{\partial \varphi}{\partial t} = \frac{2e V(t)}{\hbar}$$



$$V = \frac{\Phi_0}{2\pi \cdot I_c \cdot \cos\varphi} \cdot \frac{dI}{dt} = L_J(\varphi) \cdot \frac{dI}{dt}$$

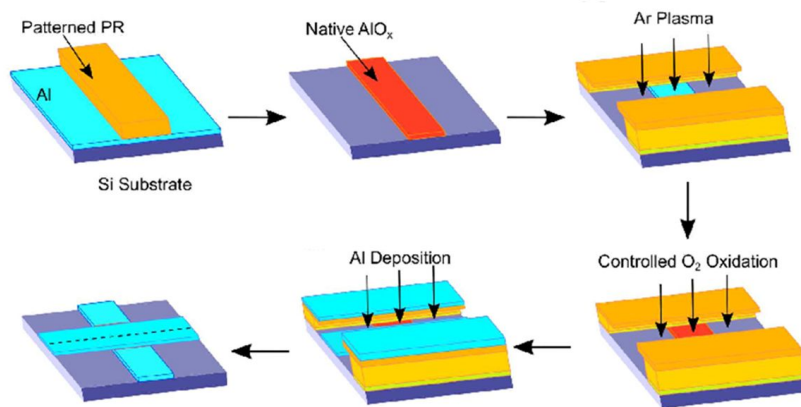
→ non-linear and tunable inductance



Cross Josephson junctions at FBK



Quantum Science and Technology in Trento



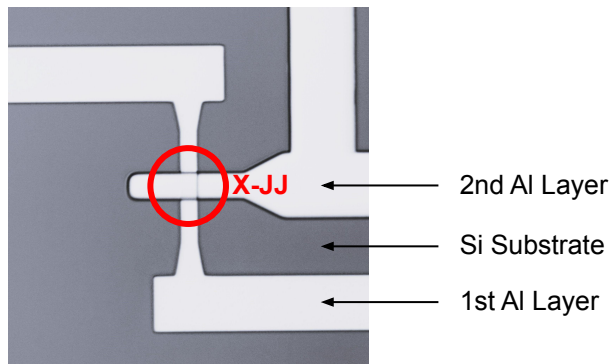
Advantages

- High control on areas (and on junction parameters)
- Two-layers process



Challenge

- Develop an efficient Ar plasma cleaning
- Optimise the second lithographic step (lift-off)



Cross Josephson junctions at FBK - 1st generation



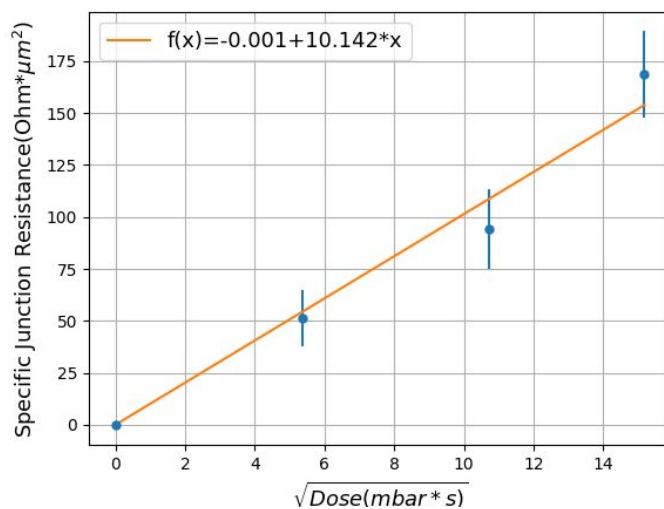
Quantum Science and Technology in Trento



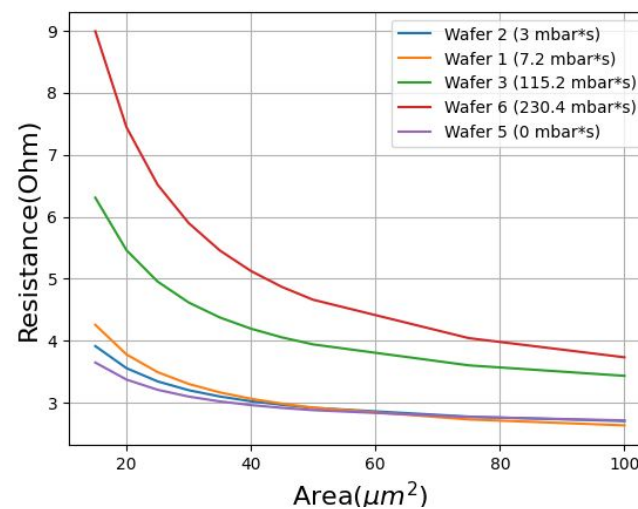
The junction normal resistance R_N is related to the critical current I_c :
 $I_c R_N = (\pi/4) \cdot V_g$

Resistance measurements at $T = 300$ K

Junction resistance vs $\sqrt{\text{oxidation dose}}$

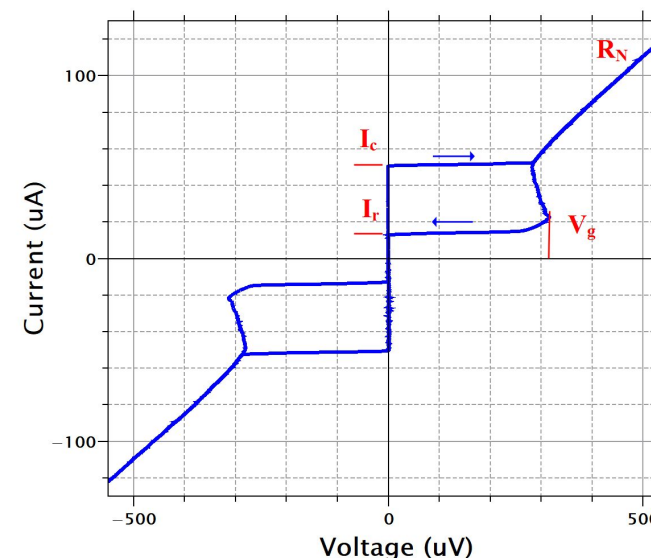


Junction resistance vs junction area (for different oxidation doses)



Cryo measurements at $T = 20$ mK

IV characteristics



Cross Josephson junctions at FBK - 2nd generation



Quantum Science and Technology in Trento

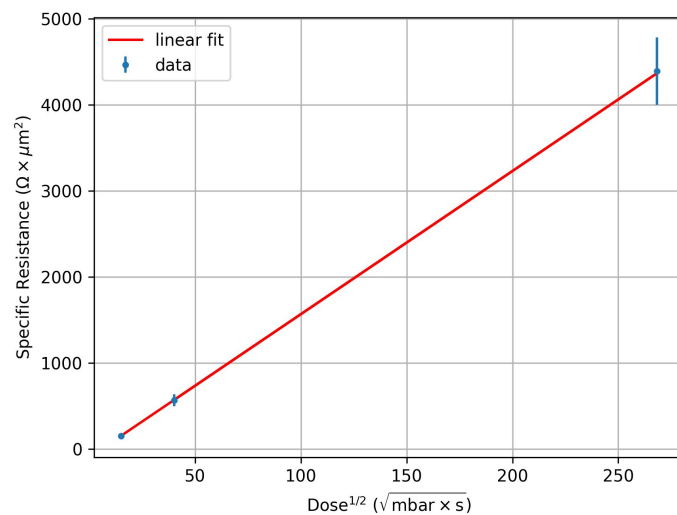


The junction normal resistance R_N is related to the critical current I_c :
 $I_c R_N = (\pi/4) \cdot V_g$

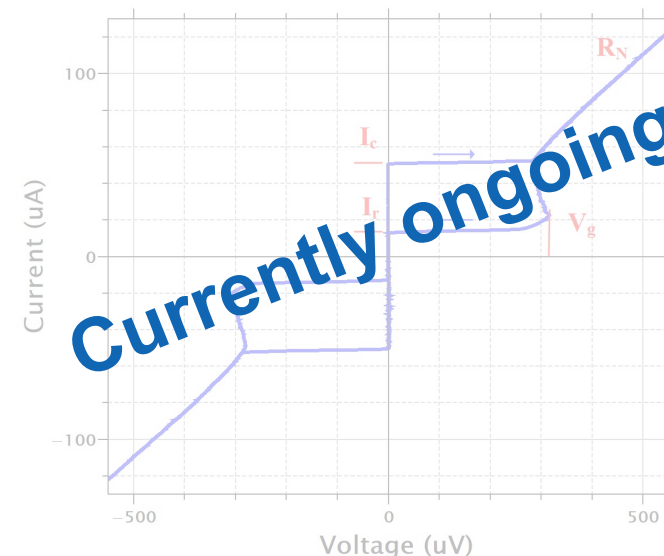
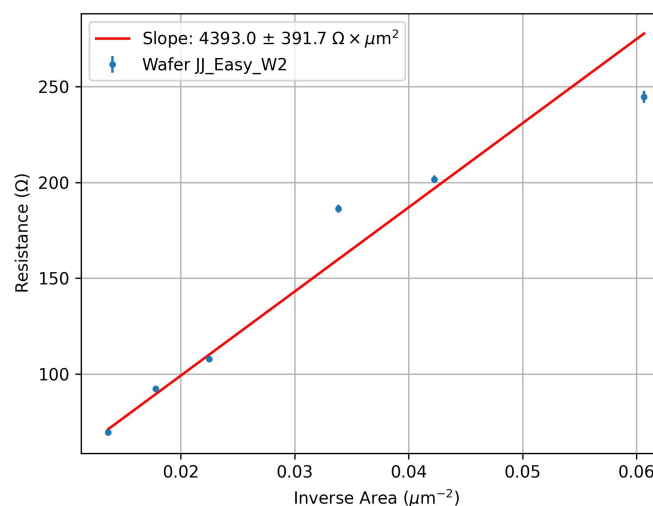
Resistance measurements at $T = 300$ K

Cryo measurements at $T = 20$ mK

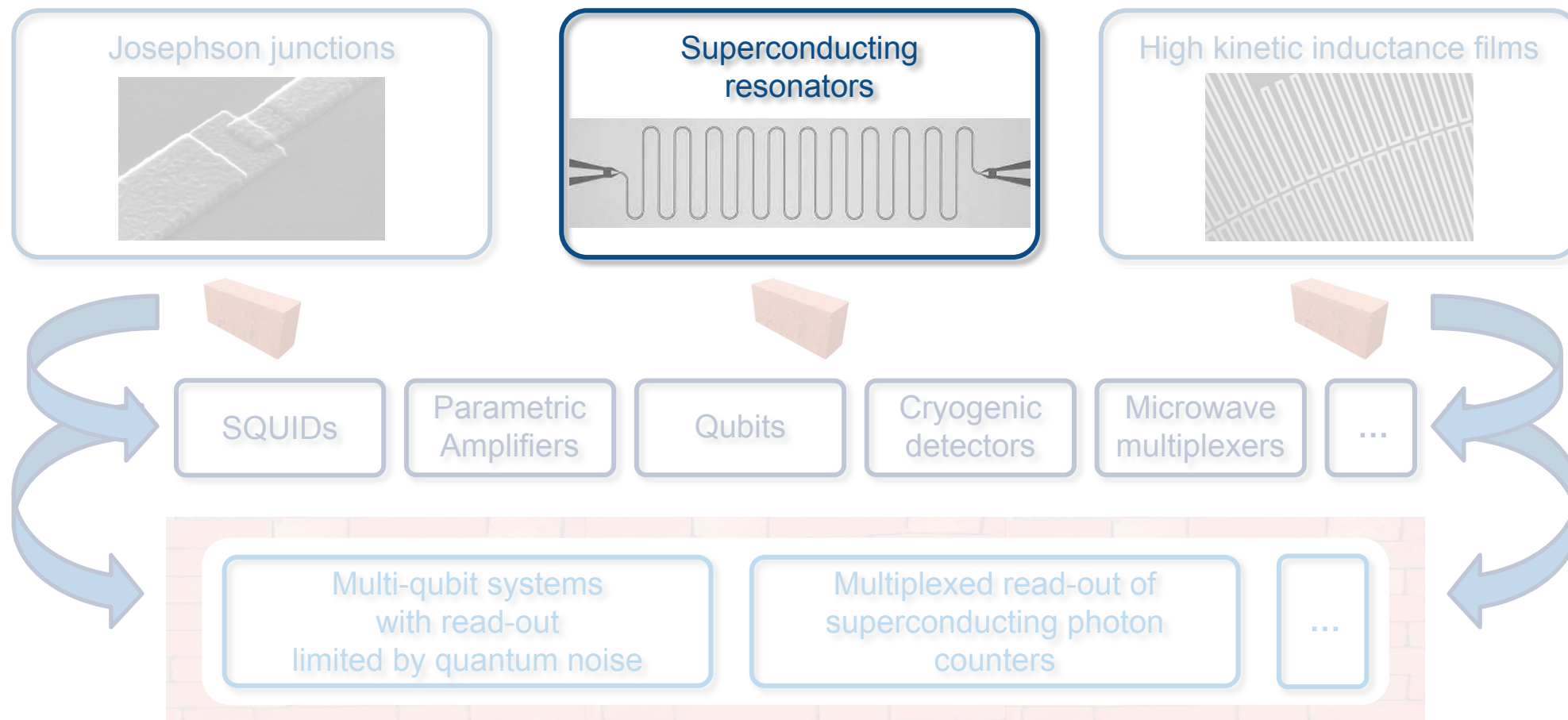
Junction resistance vs $\sqrt{\text{oxidation dose}}$



Junction resistance vs junction area



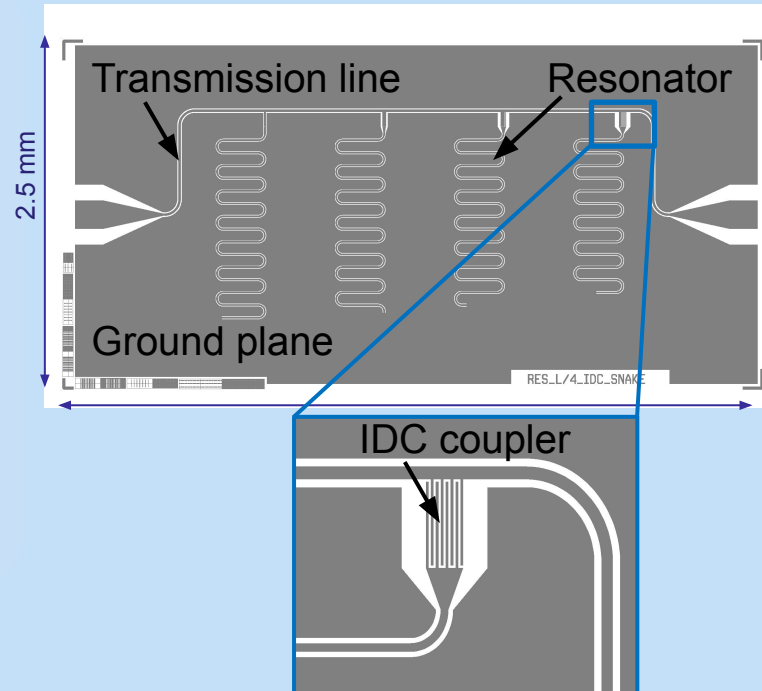
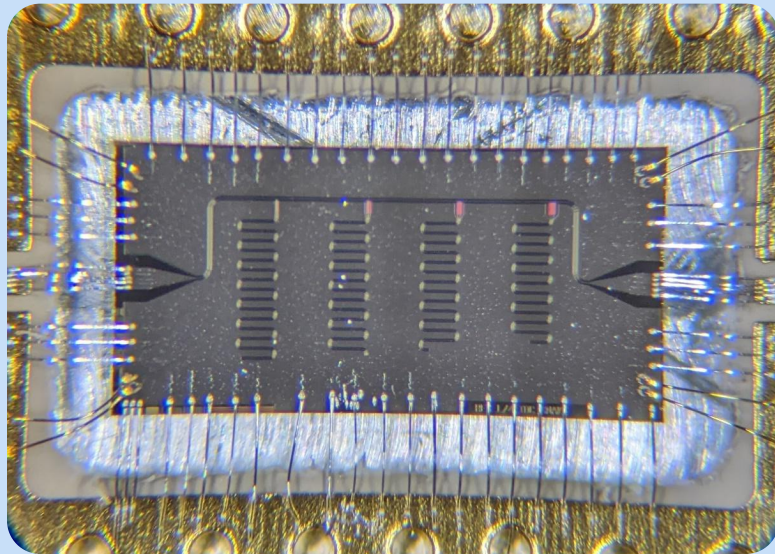
Superconducting electronics - from building blocks to integrated circuits



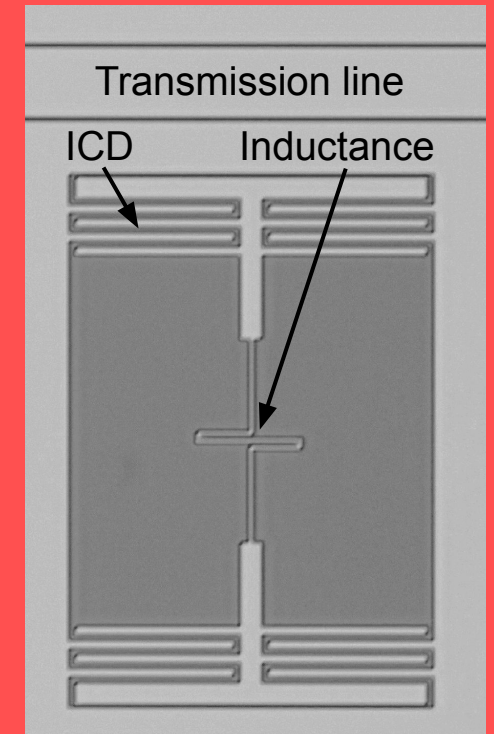


Superconducting microwave resonators

CPW quarter-wave resonators



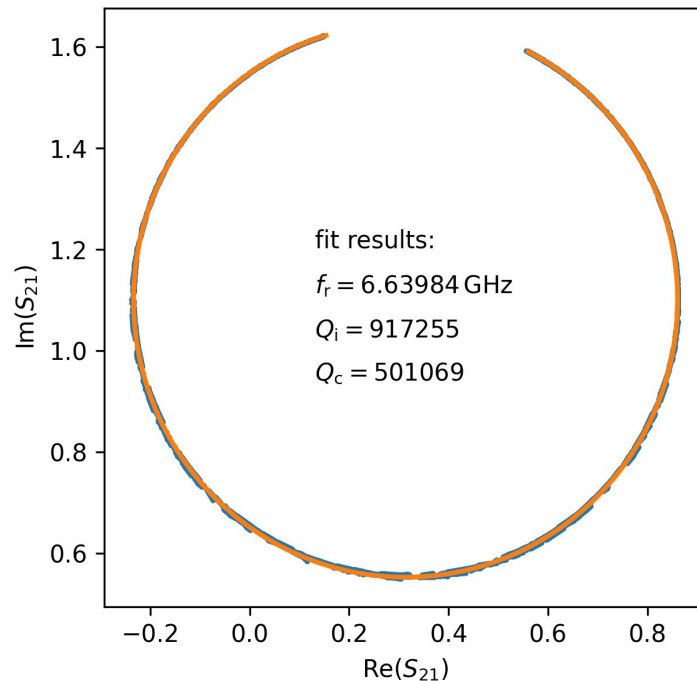
Lumped element resonators



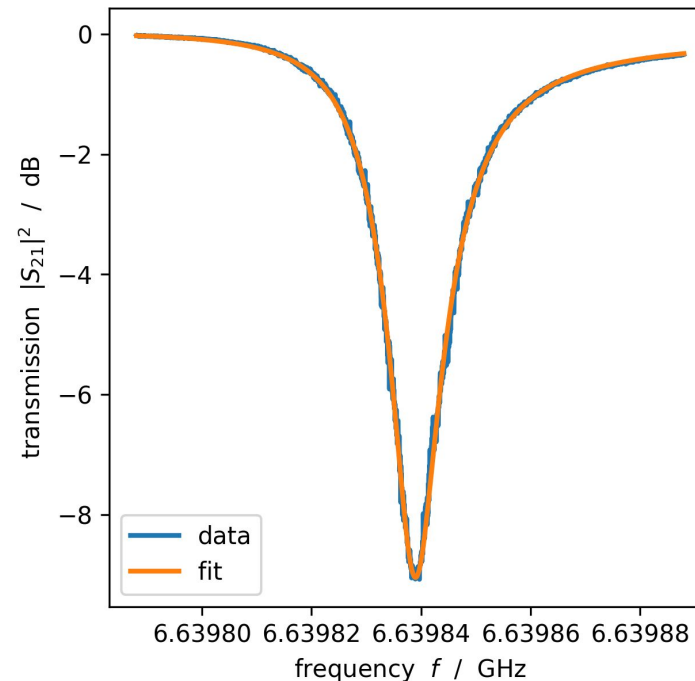


Superconducting microwave resonators

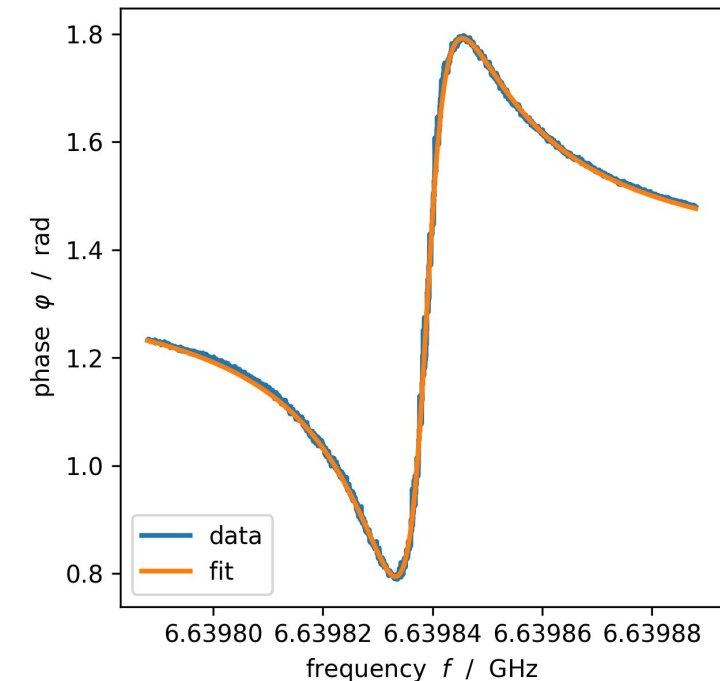
Most recent results with aluminium based lumped element resonators



Fit in complex S_{21} plane



Transmission $|S_{21}|^2$

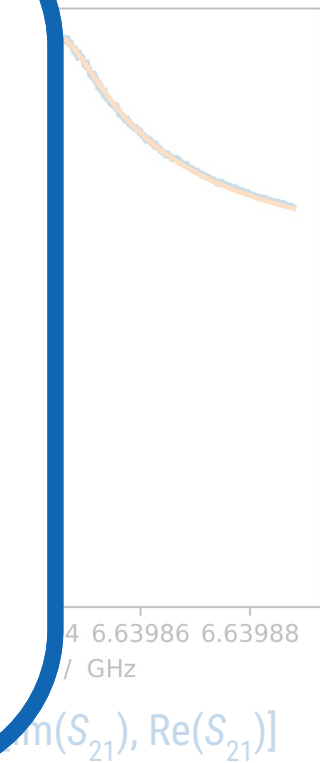
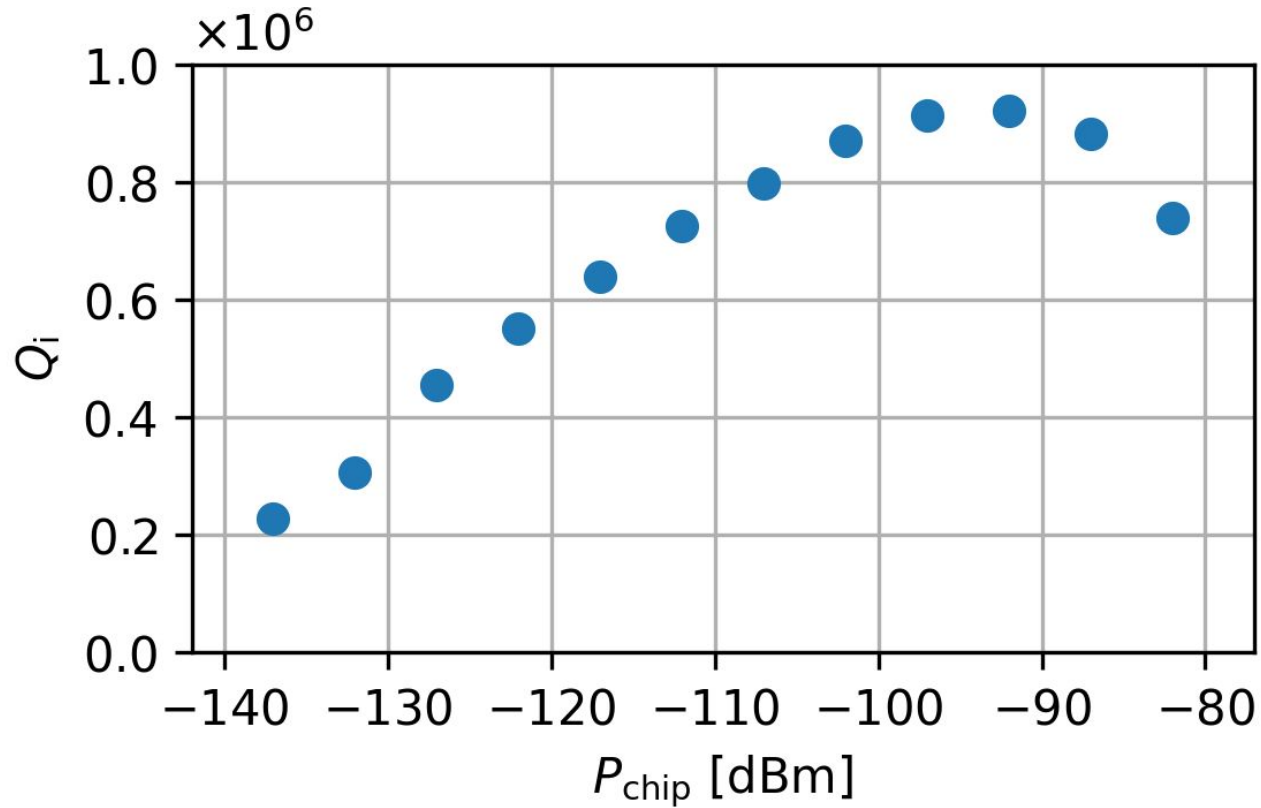
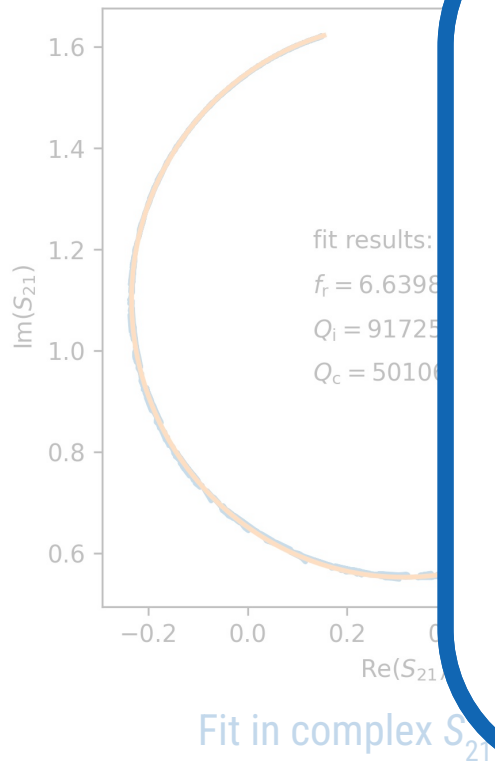


Phase $\arctan2[\text{Im}(S_{21}), \text{Re}(S_{21})]$



Superconducting microwave resonators

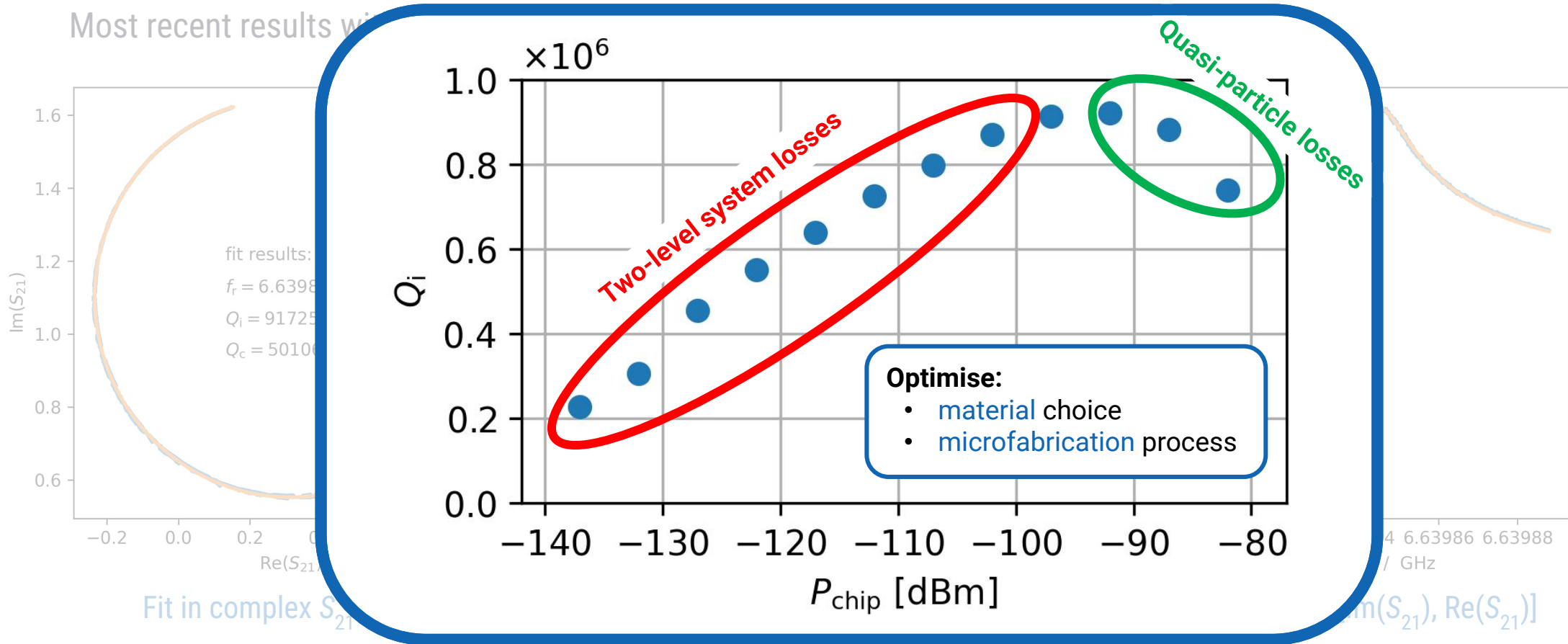
Most recent results with



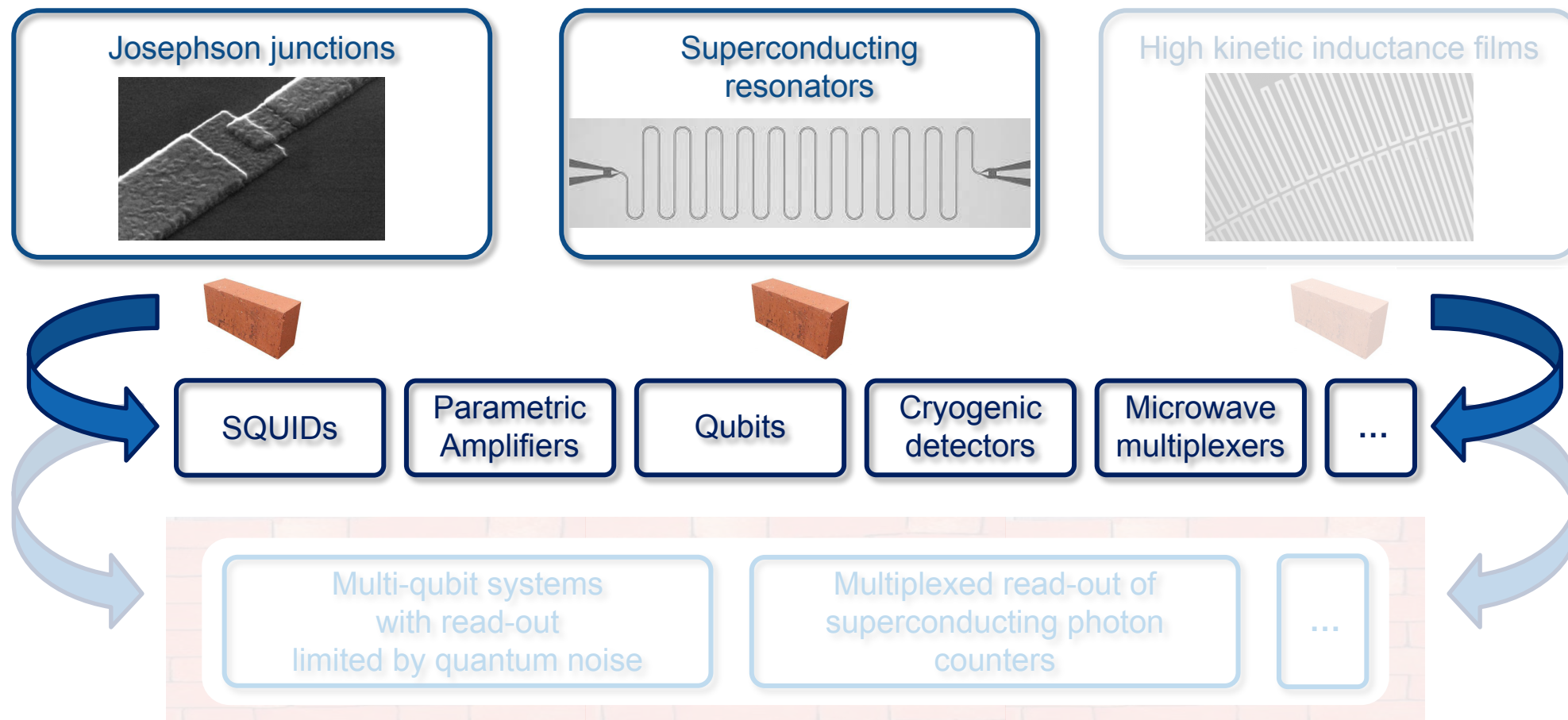


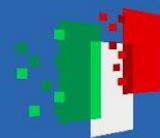
Superconducting microwave resonators

Most recent results with

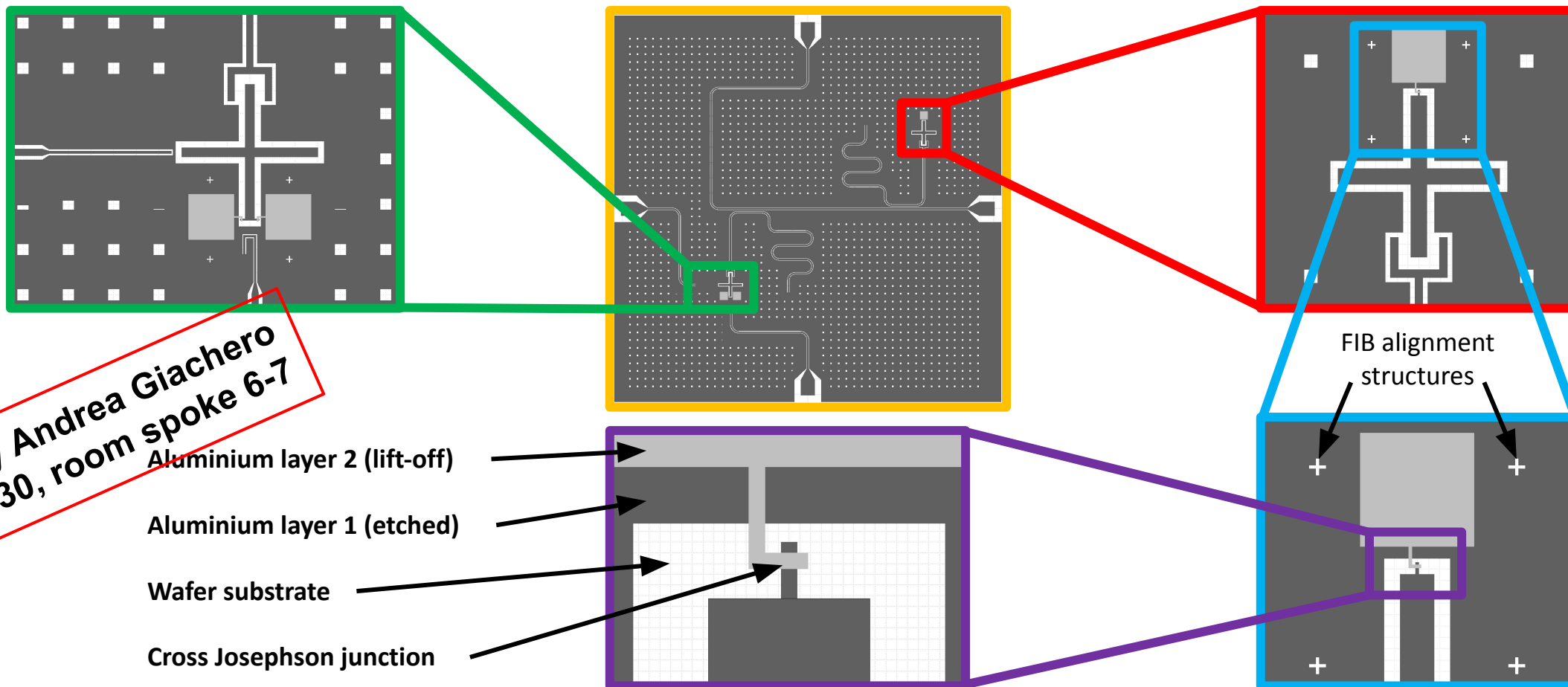


Superconducting electronics - from building blocks to integrated circuits



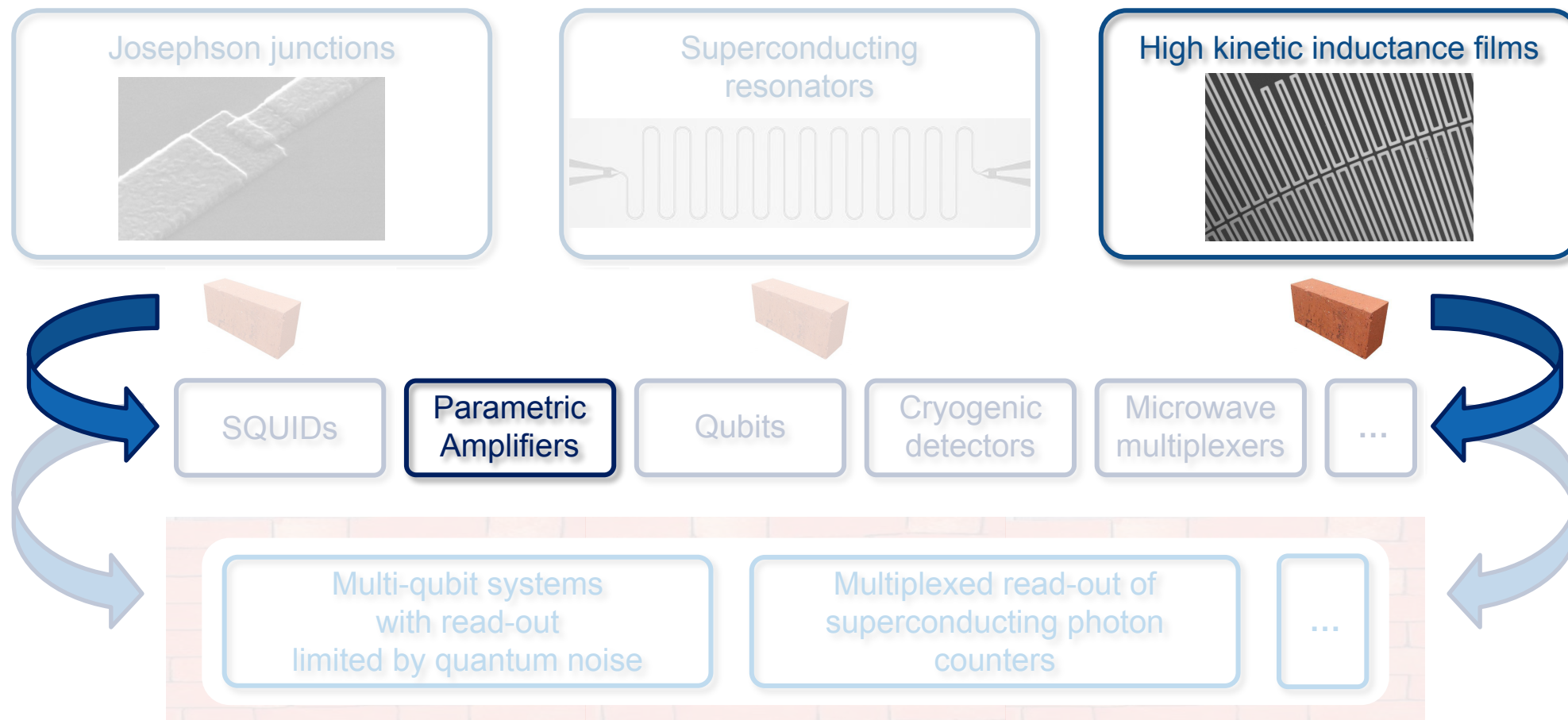


Microfabrication of qubits



Talk by Andrea Giachero
@ 11:30, room spoke 6-7

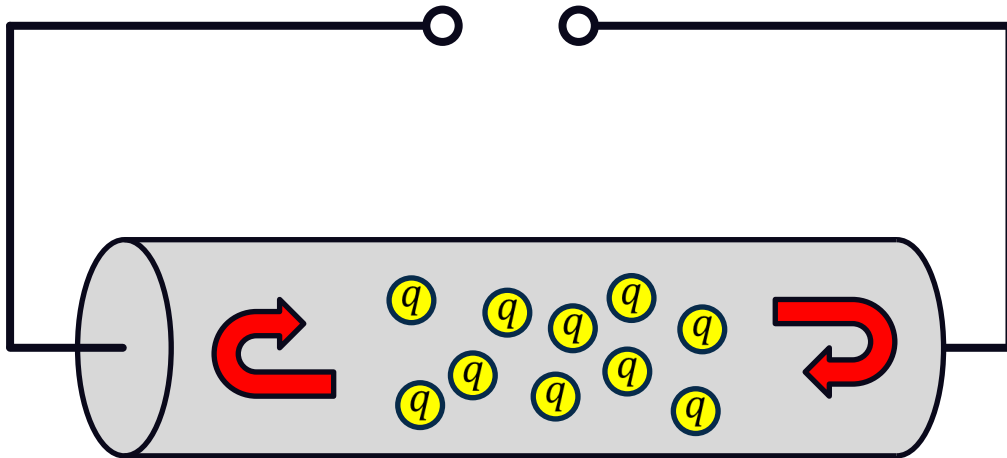
Superconducting electronics - from building blocks to integrated circuits





High kinetic inductance films

$$U = U_0 e^{i\omega t}$$



$$\sigma = \frac{nq^2\tau}{m(1 + i\omega\tau)}$$

Kinetic inductance:

- large collision time τ
- high frequency ω

Superconductor:

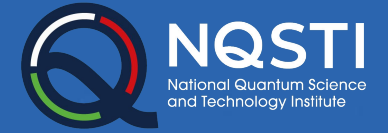
$$\tau \rightarrow \infty, \quad m = 2m_e, \quad q = 2e$$

Cooper pair density $n = n(I)$

$$\Rightarrow L(I) \approx L_0 \cdot \left(1 + \frac{I^2}{I_*^2}\right)$$

$$L_0 = \frac{R_S \hbar}{\pi \Delta}$$

$$I_* \propto 1/\sqrt{R_n}$$



High kinetic inductance films

- Interesting materials:
high-resistivity superconductors
- Our choice: **NbTiN**
 - high resistivity ($\sim 100\text{--}200\text{ m}\Omega\text{cm}$)
 - high critical temperature ($\sim 12\text{--}13\text{ K}$)

Superconductor:

$$\tau \rightarrow \infty, \quad m = 2m_e, \quad q = 2e$$

Cooper pair density $n = n(I)$

$$\Rightarrow L(I) \approx L_0 \cdot \left(1 + \frac{I^2}{I_*^2}\right)$$

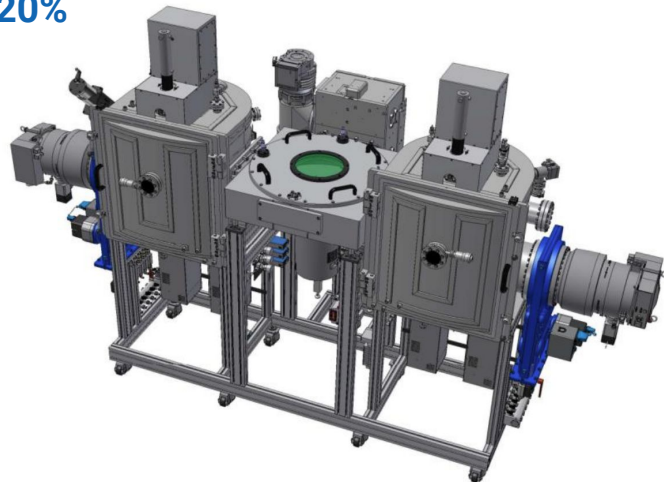
$$L_0 = \frac{R_S \hbar}{\pi \Delta}$$

$$I_* \propto 1/\sqrt{R_n}$$



Optimisation of NbTiN thin films: parameter exploration

- Sputter system:
PVD Kenosistec 800 C
- Sputter target:
Nb_{80%}Ti_{20%}



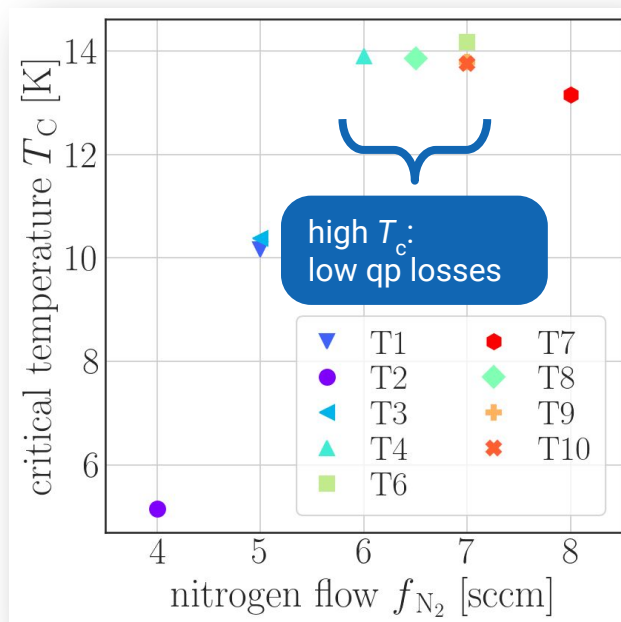
Fabrication run <i>R1</i>				
Wafer	P/W	p/mbar	$f_{\text{Ar}}/\text{sccm}$	$f_{\text{N}_2}/\text{sccm}$
T1	700	2e-3	50	5
T2	700	3e-3	50	4
T3	700	3e-3	50	5
T4	700	3e-3	50	6
T5	1200	3e-3	50	5
T6	700	3e-3	50	7
T7	700	3e-3	50	8
T8	700	3e-3	50	6.5
T9*	700	3e-3	50	7
T10	600	3e-3	50	7

* $T = 300\text{ }^\circ\text{C}$

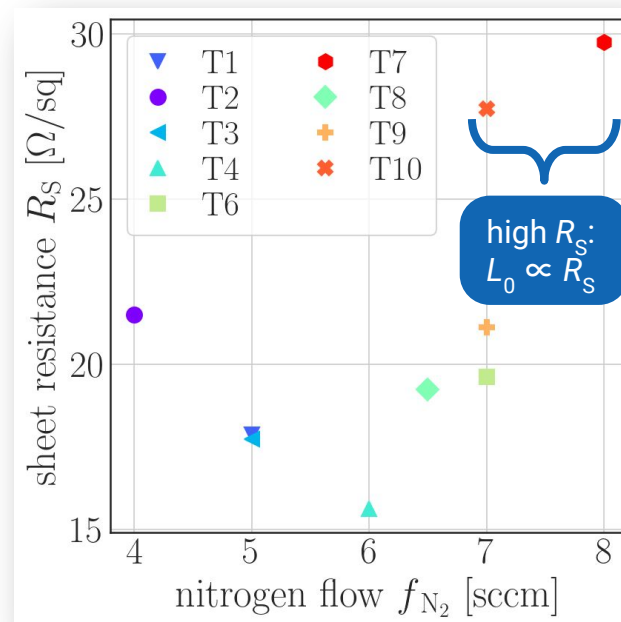


Optimisation of NbTiN thin films: parameter exploration

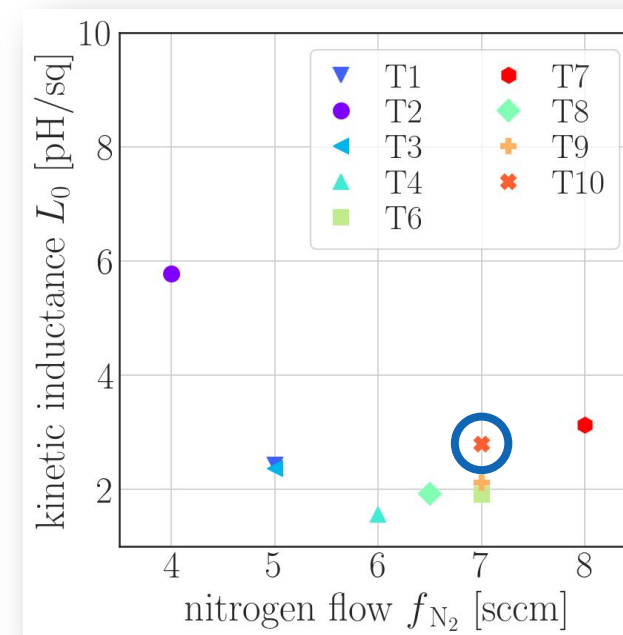
Measured T_c :



Measured R_s :



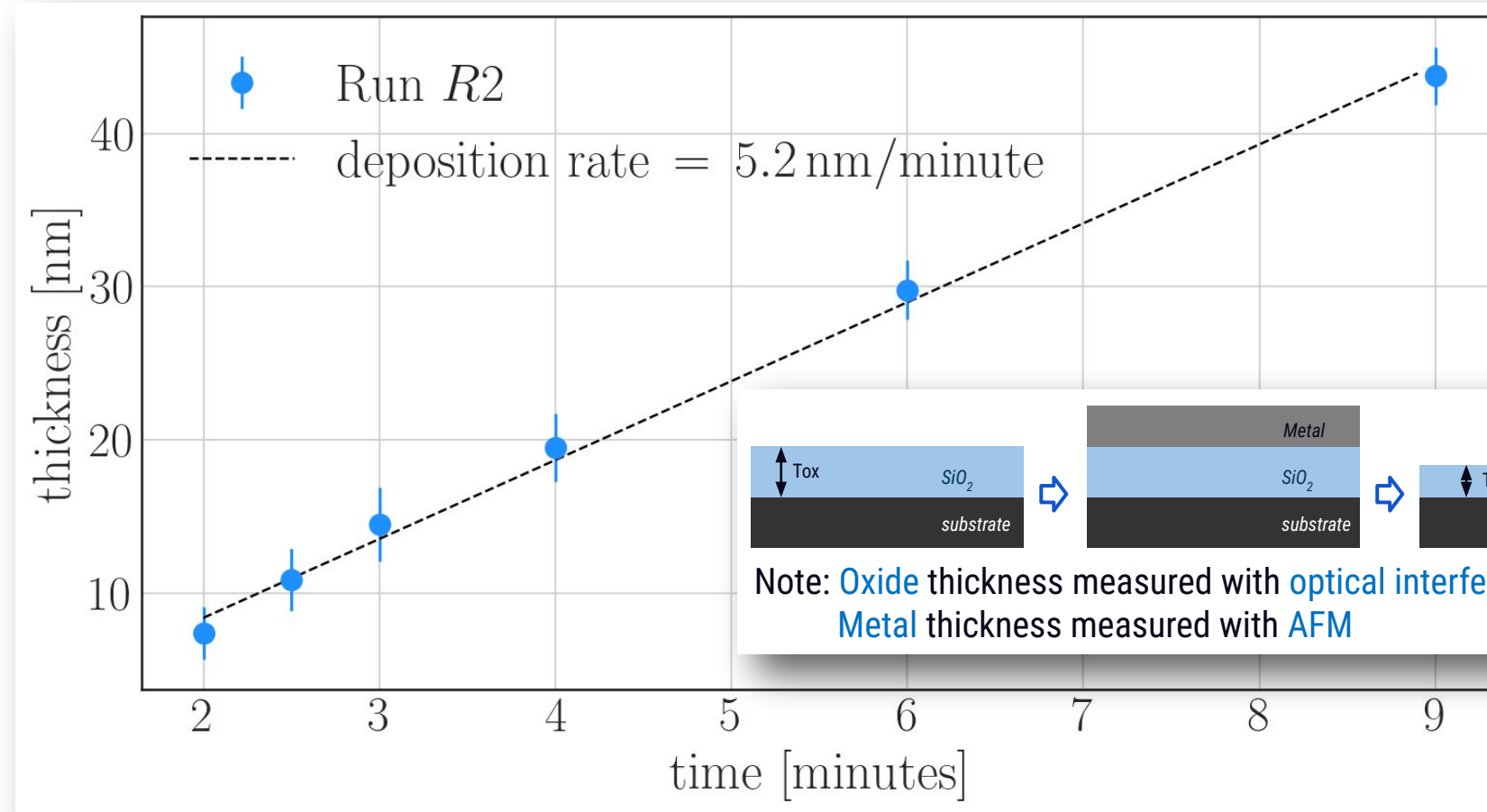
$$L_0 = \frac{R_s \cdot \hbar}{\pi \cdot T_c \cdot k_B \cdot 1.762}$$



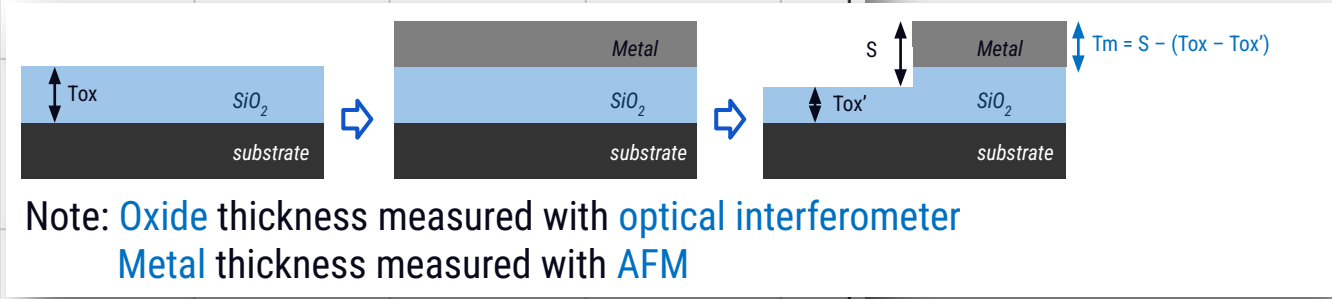
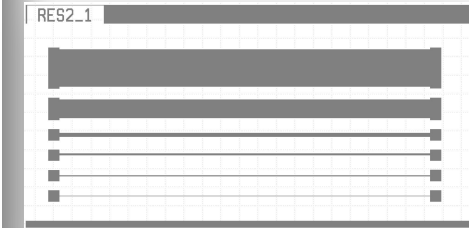
→ Recipe **T10**: high T_c and sufficiently high R_s



Calibration of NbTiN deposition rate



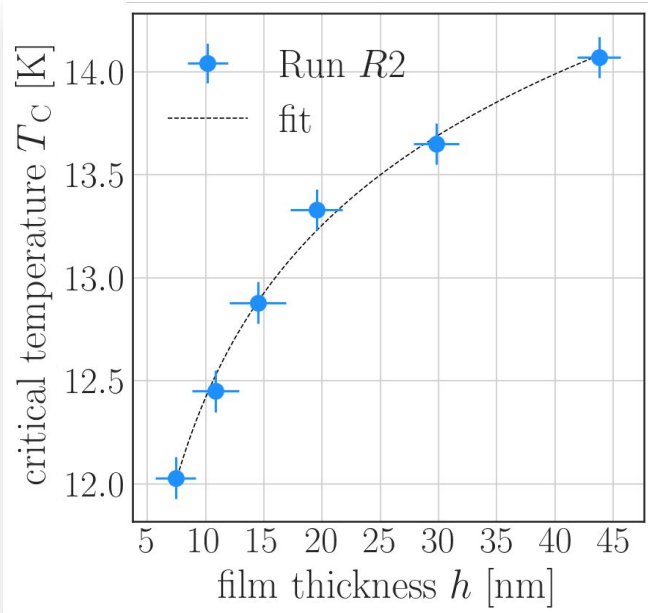
Test chip:



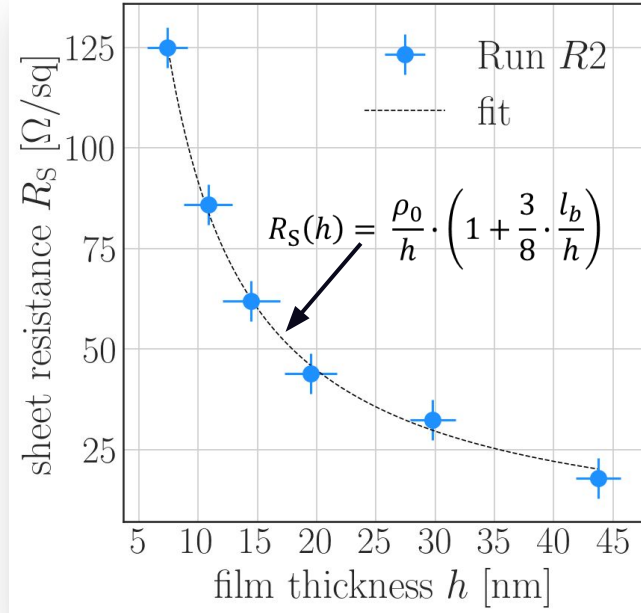


Calibrate film thickness h vs kinetic inductance L_0

Measured T_c :

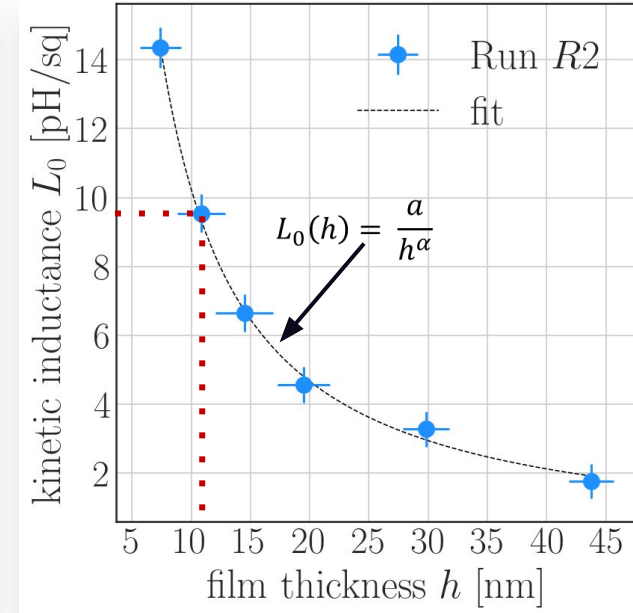


Measured R_s :



Fuchs' model (doi: 10.1017/S0305004100019952)

$$L_0 = \frac{R_s \cdot \hbar}{\pi \cdot T_c \cdot k_B \cdot 1.762}$$



Phenomenological model

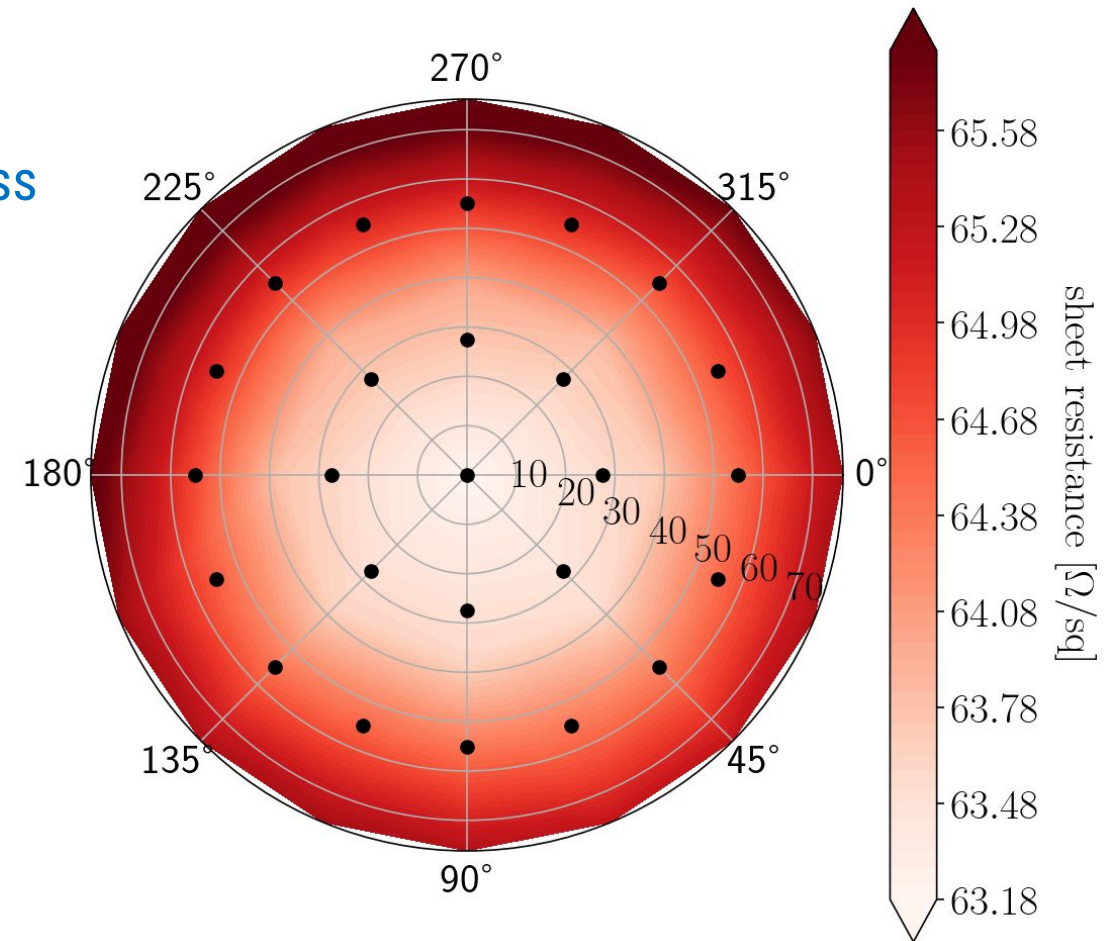
→ Use film thickness h as L_0 tuning parameter



Uniformity on wafer scale

Estimation of the uniformity of the **film thickness**

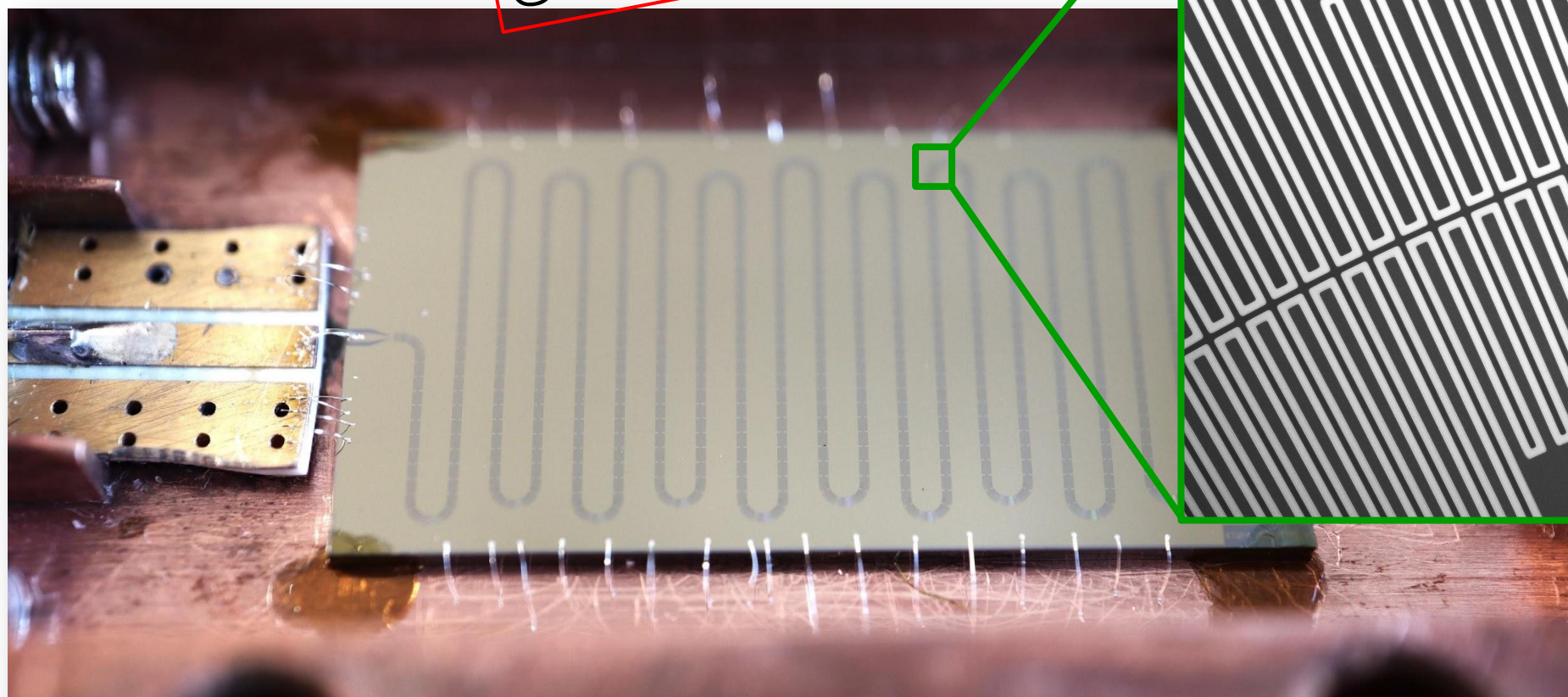
- Measurement of the **sheet resistance** (25 points over the 6 " wafer)
- Variation is about **4%**
- **Radial gradient** (thinner film at the edge)





KI-TWPAs

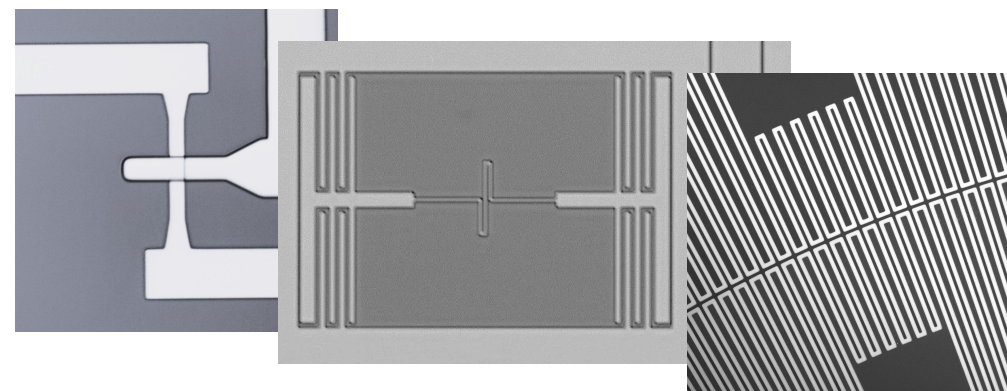
Talk by Federica Mantegazzini
@ 9:45, room spoke 6-7



Conclusion

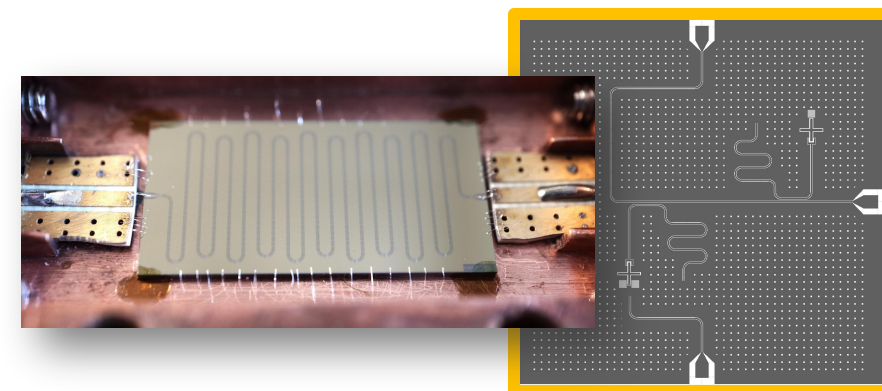
Building blocks ready:

- Josephson junctions
- Microwave resonators
- High kinetic inductance films



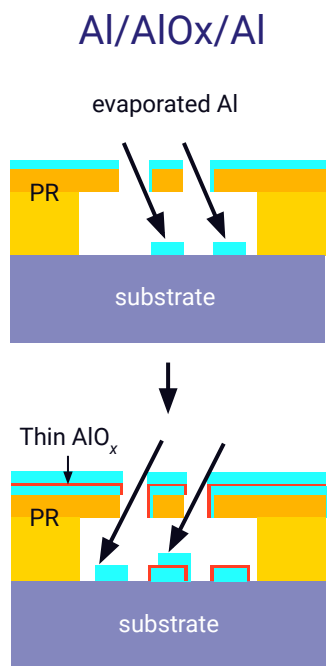
Currently ongoing:

- Further improvement of building blocks
- Integrating building blocks into circuits



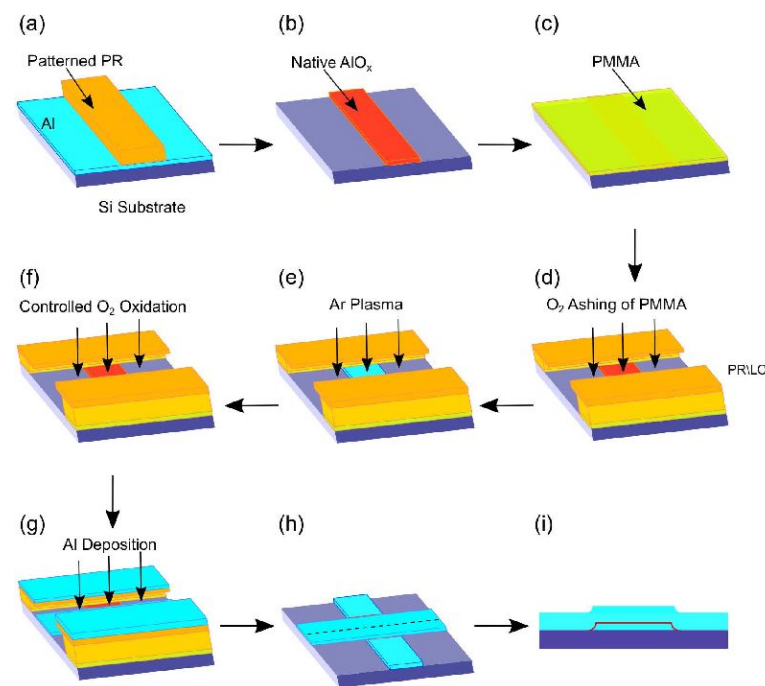
How to microfabricate Josephson junctions

Dolan technique (aka shadow evaporation)



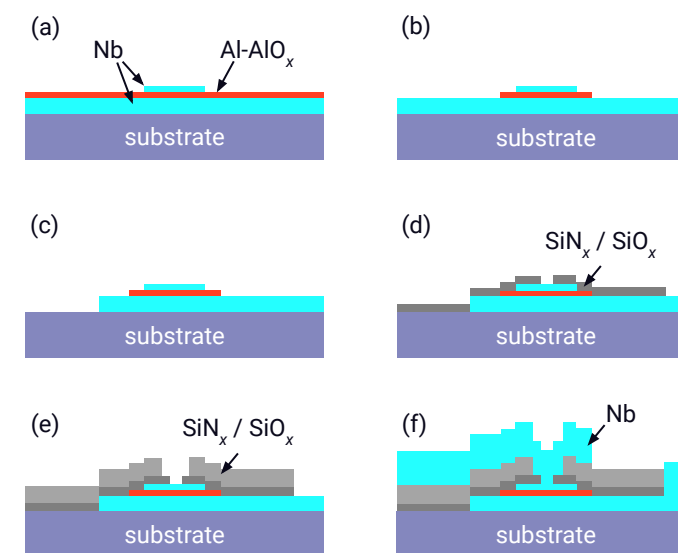
Cord B. et al (2006) 10.1116/1.2375090

Cross junctions Al/AIO_x/Al



Bal M. et al (2021) 10.1063/5.0048621

Window-type / Trilayer Nb/Al-AIO_x/Nb



Kempf S. et al (2013) 10.1088/0953-2048/26/6/065012